PROCESS CPD17

Ultra Fast Rectifier

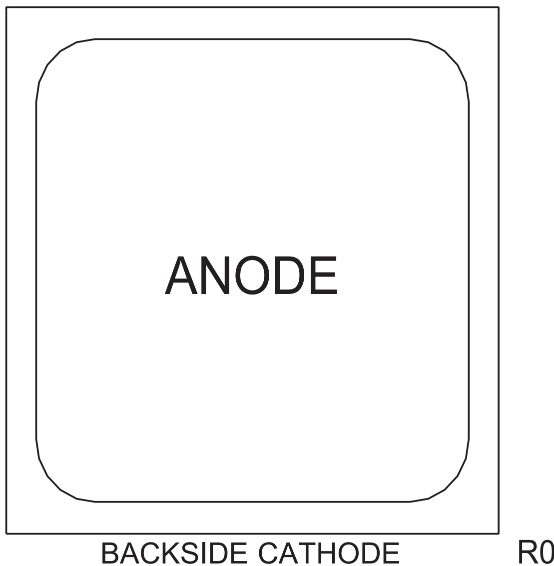
3 Amp Glass Passivated Rectifier Chip

www.DataSheet4U.com

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	88 x 88 MILS
Die Thickness	14 MILS
Anode Bonding Pad Area	69 x 69 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

GEOMETRY

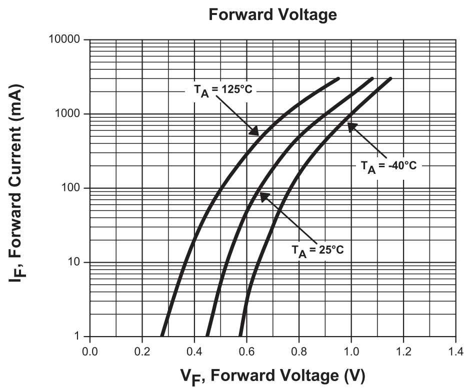


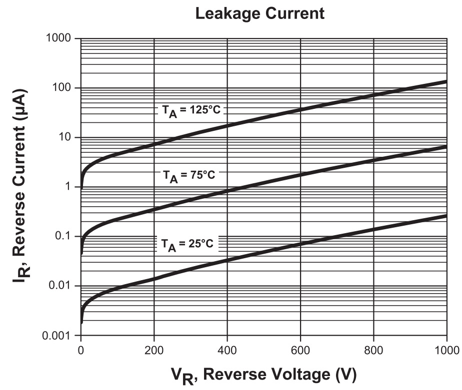
GROSS DIE PER 4 INCH WAFER
1,200

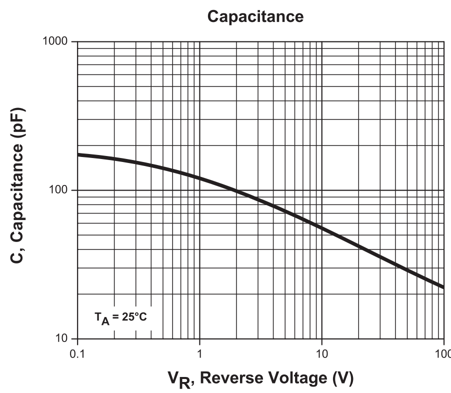
PRINCIPAL DEVICE TYPES
1N5802 thru 1N5806
UES1101 thru UES1106
CMR3U-01 Series

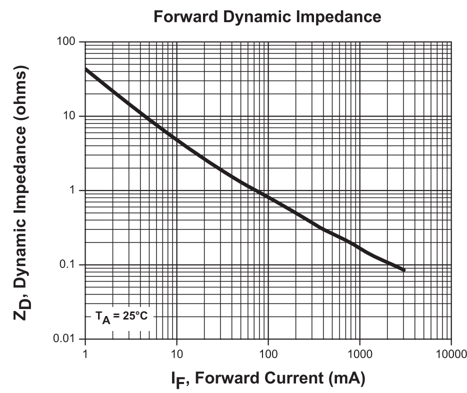
PROCESS CPD17

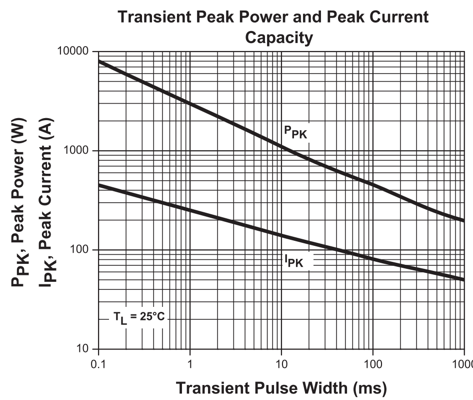
Typical Electrical Characteristics

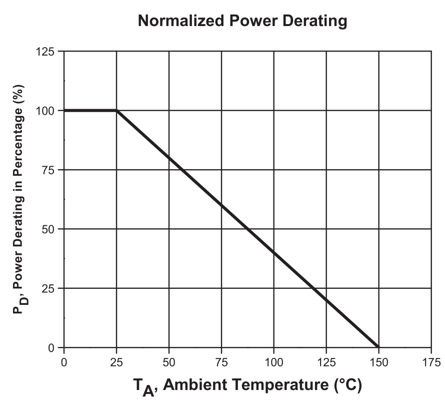












R4 (22-March 2010)